TOSHIBA CMOS Didital Integrated Circuit Silicon Monolithic

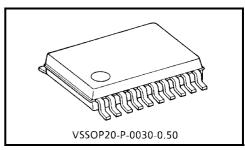
# TC7MET240AFK, TC7MET244AFK

Octal Bus Buffer

TC7MET240AFK Inverted, 3-State Outputs TC7MET244AFK Non-Inverted, 3-State Outputs

The TC7MET240AFK and 244AFK are advanced high speed CMOS octal bus buffers fabricated with silicon gate  $\mathrm{C}^2\mathrm{MOS}$  technology. They achieve the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

The TC7MET240AFK is an inverting 3-state buffer having two active-low output enables. TC7MET244AFK is a non-inverting 3-state buffer, and has two active-low output enables.



Weight: 0.03 g (typ.)

These devices are designed to be used with 3-state memory address drivers, etc.

The input voltage are compatible with TTL output voltage.

These devices may be used as a level converter for interfacing 3.3 V to 5 V system.

Input protection and output circuit ensure that 0 to 5.5 V can be applied to the input and output (\*) pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

\*: output in off-state

#### **Features**

- High speed:  $t_{pd} = 5.6 \text{ ns (typ.)} (V_{CC} = 5 \text{ V})$
- Low power dissipation:  $ICC = 4 \mu A \text{ (max) (Ta} = 25 \text{°C)}$
- Compatible with TTL outputs: VIL = 0.8 V (max)VIH = 2.0 V (min)
- Power down protection is provided on all inputs and outputs.
- Balanced propagation delays:  $t_pLH \approx t_pHL$
- Low noise: VOLP = 1.0 V (max)
- Pin and function compatible with the 74 series (74AC/HC/F/ALS/LS etc.) 240/244 type.

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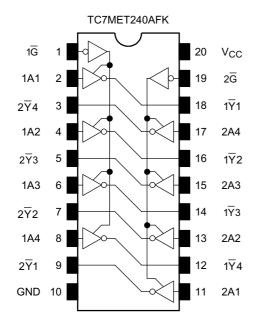
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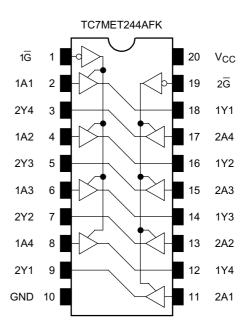
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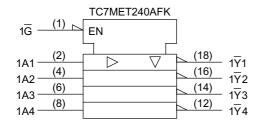
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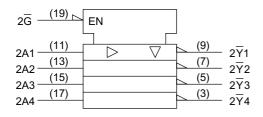
#### Pin Assignment (top view)

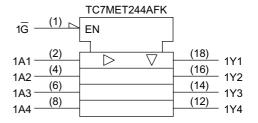


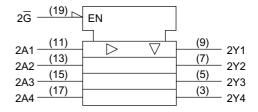


### **IEC Logic Symbol**









#### **Truth Table**

Inp	uts	Outputs			
G	A <sub>n</sub>	Yn	$\overline{Y}_n$		
L	L	L	Н		
L	Н	Н	L		
Н	Х	Z	Z		

X: Don't care

Z: High impedance

Yn: TC7MET244AFK

 $\overline{Y}_n$ : TC7MET240AFK



## **Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	V	-0.5~7.0 (Note1)	V
DC output voltage	Vout	-0.5~V <sub>CC</sub> + 0.5 (Note2)	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	lok	±20 (Note3)	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

Note1: Output in off-state

Note2: High or low state. I<sub>OUT</sub> absolute maximum rating must be observed.

Note3:  $V_{OUT} < GND, V_{OUT} > V_{CC}$ 

## **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit	
Supply voltage	V <sub>CC</sub>	4.5~5.5	V	
Input voltage	V <sub>IN</sub>	0~5.5	٧	
Output voltage	Vout	0~5.5 (Note4)	V	
Output voltage	VOU1	0~V <sub>CC</sub> (Note5)		
Operating temperature	T <sub>opr</sub>	-40~85	°C	
Input rise and fall time	dt/dv	0~20	ns/V	

Note4: Output in off-state Note5: High or low state



#### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics		Symbol Test Condition			Ta = 25°C			Ta = -4	Unit		
		Symbol	rest Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
Input voltage	High level	V <sub>IH</sub>	_		4.5~5.5	2.0	_	_	2.0	_	V
input voitage	Low level	V <sub>IL</sub>		_	4.5~5.5	_	_	8.0	_	0.8	V
Llink lavel	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub>	$I_{OH} = -50 \mu A$	4.5	4.4	4.5		4.4	_		
Output voltage	High level	VOH	or V <sub>IL</sub>	$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	٧
Output voltage L	Low level	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OL} = 50  \mu A$	4.5	_	0	0.1	_	0.1	
				I <sub>OL</sub> = 8 mA	4.5	_	_	0.36	_	0.44	
3-state output off-state current $I_{OZ}$ $V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND		5.5	_	_	±0.25	_	±2.50	μА			
Input leakage cu	ırrent	I <sub>N</sub>	V <sub>IN</sub> = 5.5 V or GND		0~5.5		_	±0.1	_	±1.0	μΑ
		I <sub>CC</sub>	$V_{IN} = V_{CC}$ or GND		5.5	_	_	4.0	_	40.0	μА
Quiescent supply current		ICCT	Per input: V <sub>IN</sub> = 3.4 V Other input: V <sub>CC</sub> or GND		5.5	_	_	1.35	_	1.50	mA
Output leakage	current	I <sub>OPD</sub>	V <sub>OUT</sub> = 5.5 V		0		_	0.5		5.0	μΑ

### AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Symbol Test Condition				Ta = 25°C			Ta = -40~85°C		
Characteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Unit	
Propagation delay time	t <sub>pLH</sub>	t <sub>pLH</sub>	5.0 ± 0.5	15	_	5.6	7.8	1.0	9.0	ns	
(TC7MET240AFK)	tpHL	_	3.0 ± 0.3	50	_	6.1	8.8	1.0	10.0	113	
Propagation delay time	t <sub>pLH</sub>		5.0 ± 0.5	15	_	5.4	7.4	1.0	8.5	ns	
(TC7MET244AFK)	tpHL	_	5.0 ± 0.5	50		5.9	8.4	1.0	9.5		
3-state output enable time	t <sub>pZL</sub> R <sub>L</sub> = 1 kO	$R_L = 1 k\Omega$	5.0 ± 0.5	15		7.7	10.4	1.0	12.0	ns	
3-state output enable time	t <sub>pZH</sub>	KL = 1 K22		50		8.2	11.4	1.0	13.0		
3-state output disable time	t <sub>pLZ</sub> t <sub>pHZ</sub>	$R_L = 1 \text{ k}\Omega$	$5.0 \pm 0.5$	50		8.8	11.4	1.0	13.0	ns	
Output to output skew	t <sub>osLH</sub> t <sub>osHL</sub>	(Note6)	$5.0 \pm 0.5$	50	1		1.0	_	1.0	ns	
Input capacitance	C <sub>IN</sub>	_		_	4	10	_	10	pF		
Output capacitance	C <sub>OUT</sub>	<del>-</del>			9				pF		
Power dissipation capacitance (Note7)	C <sub>PD</sub>	TC7MET240AFK				19				pF	
	OPD	TC7MET244AFK		_	18	_	_	_	ρι		

Note6: Parameter guaranteed by design.

 $t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|$ 

Note7: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

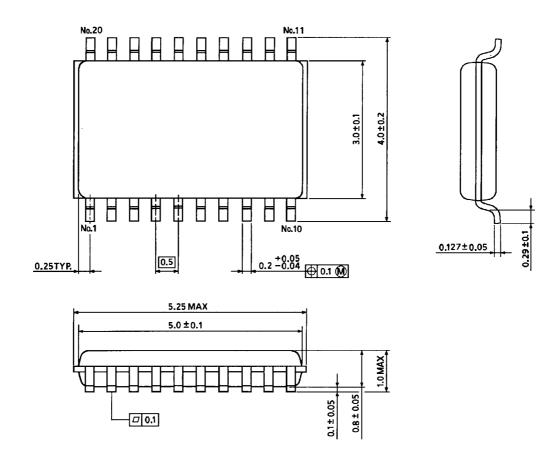
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$ 



## Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition	Ta =		25°C	Unit
Characteristics	Syllibol	rest Condition	V <sub>CC</sub> (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V <sub>OL</sub>	V <sub>OLP</sub>	C <sub>L</sub> = 50 pF	5.0	8.0	1.0	V
Quiet output minimum dynamic V <sub>OL</sub>	V <sub>OLV</sub>	C <sub>L</sub> = 50 pF	5.0	-0.8	-1.0	V
Minimum high level dynamic input voltage $V_{\mbox{\scriptsize IH}}$	V <sub>IHD</sub>	C <sub>L</sub> = 50 pF	5.0	_	2.0	V
Maximum high level dynamic input voltage $V_{\text{IL}}$	V <sub>ILD</sub>	C <sub>L</sub> = 50 pF	5.0	_	0.8	٧

## **Package Dimensions**



Weight: 0.03 g (typ.)